Electronic Supplementray Information (ESI)

Insighting Luminescence Quenching and Detecting Trap Distribution in $Ba_2Si_5N_8:Eu^{2+}$ Phosphor with Comprehensive Considerations of Temperature-Dependent Luminescence Behaviors

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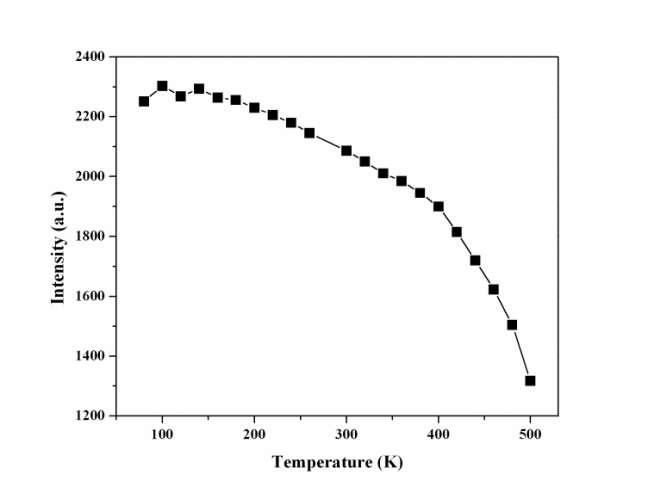

Figure S1. PL intensity as function of temperature (80-500 K).

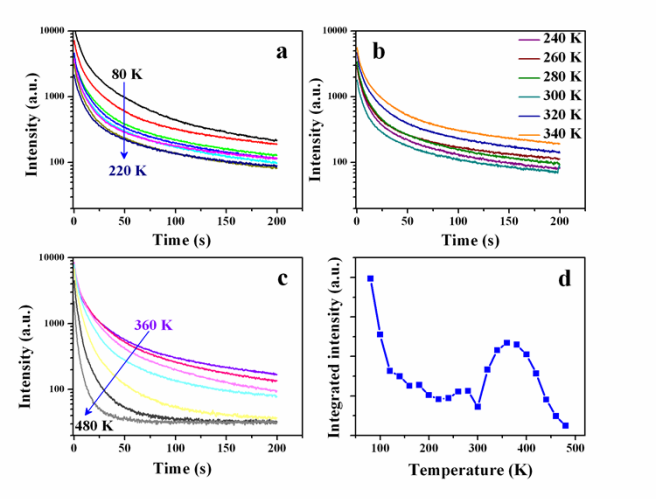

Figure S2. (a, b & c) Temperature dependence of afterglow decay curves (80-480 K) upon 300 nm excitation for 3 min, (d) dependence of integrated intensity of decay curves on temperatures. The limit time is set to 200 s.